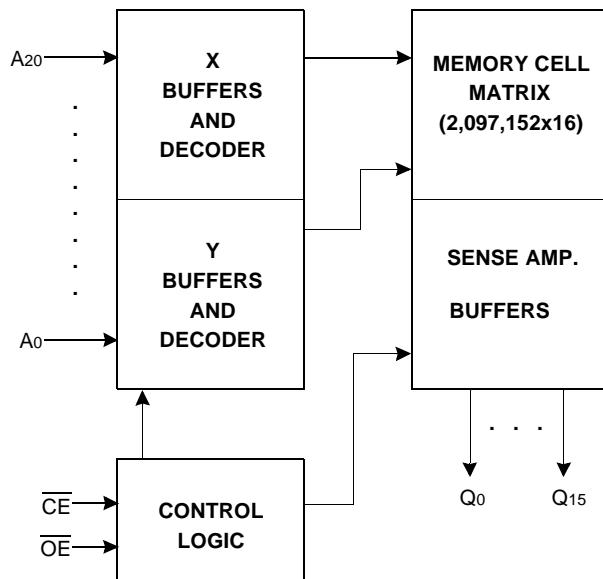


32M-Bit (2Mx16) CMOS MASK ROM

FEATURES

- 2,097,152x16 bit organization
- Fast access time
3.3V Operation : 120ns(Max.)
3.0V Operation : 150ns(Max.)
- Supply voltage : single +3.0V/ single +3.3V
- Current consumption
Operating : 40mA(Max.)
Standby : 30µA(Max.)
- Fully static operation
- All inputs and outputs TTL compatible
- Three state outputs
- Package
-. K3N6V(U)4000C-DC : 42-DIP-600

FUNCTIONAL BLOCK DIAGRAM



Pin Name	Pin Function
A0 - A20	Address Inputs
Q0 - Q15	Data Outputs
CE	Chip Enable
OE	Output Enable
Vcc	Power
Vss	Ground

GENERAL DESCRIPTION

The K3N6V(U)4000C-DC is a fully static mask programmable ROM organized 2,097,152x16 bit. It is fabricated using silicon-gate CMOS process technology.

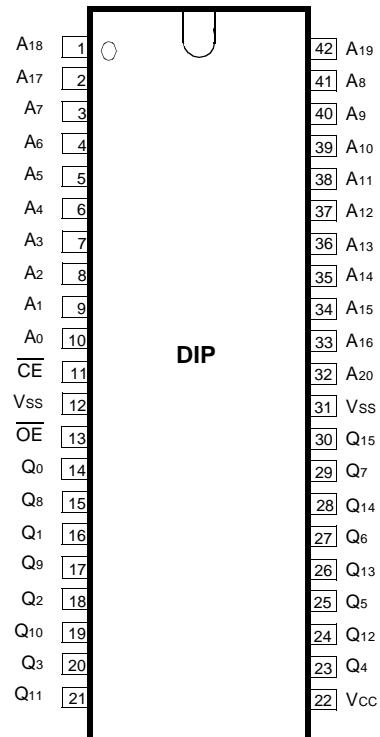
This device operates with 3.0V or 3.3V power supply, and all inputs and outputs are TTL compatible.

Because of its asynchronous operation, it requires no external clock assuring extremely easy operation.

It is suitable for use in program memory of microprocessor and data memory, character generator.

The K3N6V(U)4000C-DC is packaged in a 42-DIP.

PIN CONFIGURATION



K3N6V(U)4000C-DC



ELECTRONICS

ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss	VIN	-0.3 to +4.5	V
Temperature Under Bias	TBIAS	-10 to +85	°C
Storage Temperature	TSTG	-55 to +150	°C

NOTE : Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS(Voltage reference to Vss, TA=0 to 70°C)

Item	Symbol	Min	Typ	Max	Unit
Supply Voltage	Vcc	2.7/3.0	3.0/3.3	3.3/3.6	V
Supply Voltage	Vss	0	0	0	V

DC CHARACTERISTICS

Parameter	Symbol	Test Conditions		Min	Max	Unit	
Operating Current	Icc	$\overline{CE}=\overline{OE}=VIL$, all outputs open		Vcc=3.3V±0.3V	-	40	mA
				Vcc=3.0V±0.3V		35	mA
Standby Current(TTL)	ISB1	$\overline{CE}=Vih$, all outputs open			500	μA	
Standby Current(CMOS)	ISB2	$\overline{CE}=Vcc$, all outputs open			30	μA	
Input Leakage Current	ILI	VIN=0 to Vcc		-	10	μA	
Output Leakage Current	ILO	VOUT=0 to Vcc		-	10	μA	
Input High Voltage, All Inputs	VIH			2.0	Vcc+0.3	V	
Input Low Voltage, All Inputs	VIL			-0.3	0.6	V	
Output High Voltage Level	VOH	IOH=-400μA		2.4	-	V	
Output Low Voltage Level	VOL	IOL=2.1mA		-	0.4	V	

NOTE : Minimum DC Voltage(VIL) is -0.3V an input pins. During transitions, this level may undershoot to -2.0V for periods <20ns.

Maximum DC voltage on input pins(VIH) is Vcc+0.3V which, during transitions, may overshoot to Vcc+2.0V for periods <20ns.

MODE SELECTION

CE	OE	Mode	Data	Power
H	X	Standby	High-Z	Standby
L	H	Operating	High-Z	Active
L	L	Operating	Dout	Active

CAPACITANCE(TA=25°C, f=1.0MHz)

Item	Symbol	Test Conditions	Min	Max	Unit
Output Capacitance	Cout	VOUT=0V	-	12	pF
Input Capacitance	Cin	VIN=0V	-	12	pF

NOTE : Capacitance is periodically sampled and not 100% tested.



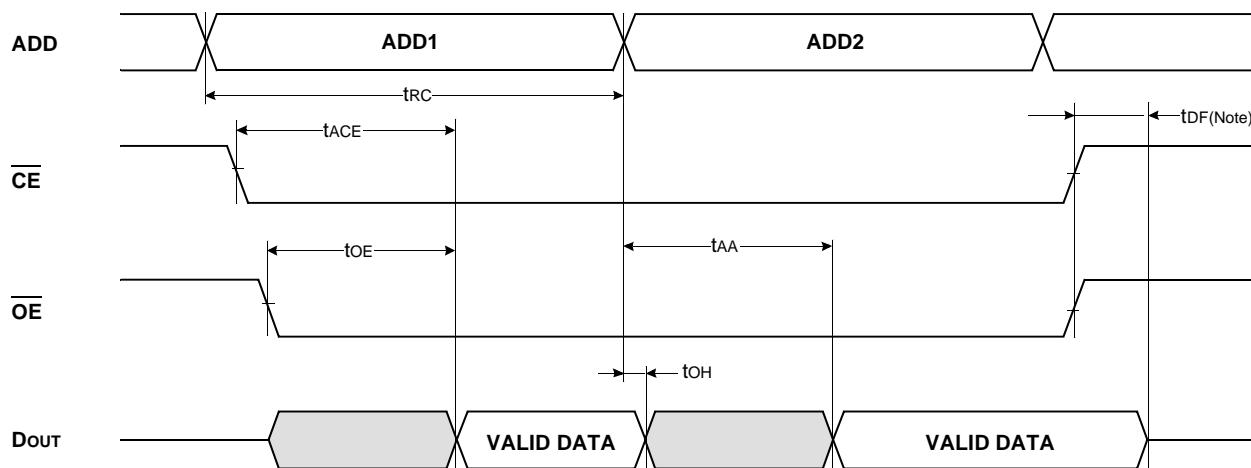
ELECTRONICS

AC CHARACTERISTICS($T_A=0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC}=3.3\text{V}/3.0\text{V}\pm0.3\text{V}$, unless otherwise noted.)**TEST CONDITIONS**

Item	Value
Input Pulse Levels	0.45V to 2.4V
Input Rise and Fall Times	10ns
Input and Output timing Levels	1.5V
Output Loads	1 TTL Gate and $C_L=100\text{pF}$

READ CYCLE

Item	Symbol	3.3V±0.3V		3.0V±0.3V		Unit
		Min	Max	Min	Max	
Read Cycle Time	t _{RC}	120		150		ns
Chip Enable Access Time	t _{ACE}		120		150	ns
Address Access Time	t _{AA}		120		150	ns
Output Enable Access Time	t _{OE}		60		70	ns
Output or Chip Disable to Output High-Z	t _{DF}		20		30	ns
Output Hold from Address Change	t _{OH}	0		0		ns

TIMING DIAGRAM**READ**

NOTE : t_{DF} is defined as the time at which the outputs achieve the open circuit condition and is not referenced to V_{OH} or V_{OL} level.



ELECTRONICS

PACKAGE DIMENSIONS

